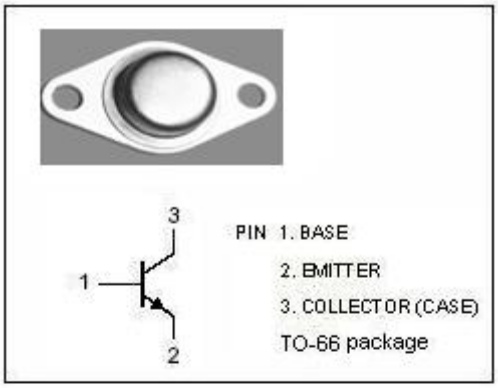
isc Silicon NPN Power Transistor 3DA76

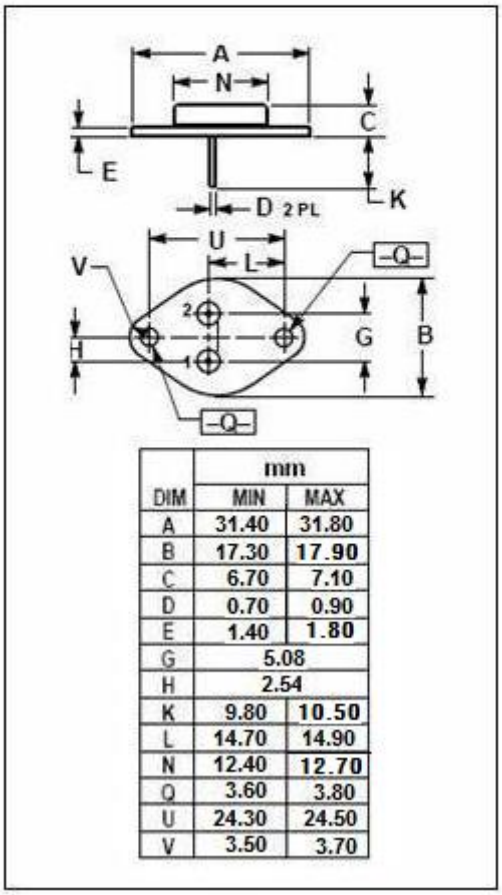
DESCRIPTION

- High DC Current Gain-
  : h_{FE}= 15(Max) @I_C= 0.3A
- Excellent Safe Operating Area
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Designed for use as an output device in complementary audio amplifiers



DIM	mm MIN	MAX
A	31.40	31.80
B	17.30	17.90
C	6.70	7.10
D	0.70	0.90
E	1.40	1.80
G	5.08	
H	2.54	
K	9.80	10.50
L	14.70	14.90
N	12.40	12.70
Q	3.60	3.80
U	24.30	24.50
V	3.50	3.70

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CEO}	Collector-Emitter Voltage	65	V
V_{EBO}	Emitter-Base Voltage	4.0	V
I_C	Collector Current-Continuous	0.5	A
P_C	Collector Power Dissipation@T_C=75℃	7.5	W
T_J	Junction Temperature	175	℃
T_{stg}	Storage Temperature Range	-55-175	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	5.0	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(BR)}$	Collector-Emitter Breakdown Voltage	I_C= 50mA; I_B=0	65		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 0.5A; I_B=0.1A		1.5	V
I_{CBO}	Emitter Cutoff current	V_{CE}= 24V; I_C=0		1.0	mA
I_{EBO}	Emitter Cutoff current	V_{EB}= 4.0V; I_C=0		0.2	mA
h_{FE}	DC Current Gain	I_C=0.3A ; V_{CE}=10V	15		